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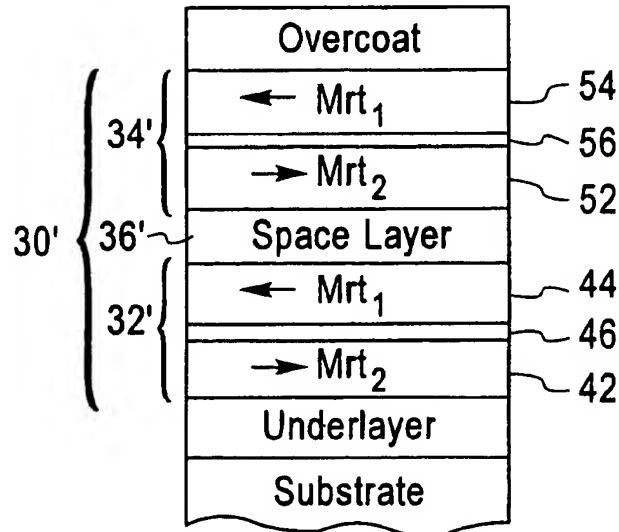
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(54) Title: LAMINATED MAGNETIC RECORDING MEDIA WITH ANTFERROMAGNETICALLY COUPLED LAYER AS ONE OF THE INDIVIDUAL MAGNETIC LAYERS IN THE LAMINATE

Laminated Media
With AFC Layers
 $M_{rt} = 2(M_{rt_1} - M_{rt_2})$



(57) Abstract: A laminated magnetic recording medium for data storage has an antiferromagnetically coupled (AFC) layer and a single ferromagnetic layer spaced apart by a nonferromagnetic spacer layer. The AFC layer is formed as two ferromagnetic films antiferromagnetically coupled together across an antiferromagnetically coupling film that has a composition and thickness to induce antiferromagnetic coupling. In each of the two remanent magnetic states, the magnetic moments of the two antiferromagnetically coupled films in the AFC layer are oriented antiparallel, and the magnetic moment of the single ferromagnetic layer and the greater-moment ferromagnetic film of the AFC layer are oriented parallel. The nonferromagnetic spacer layer between the AFC layer and the single ferromagnetic layer has a composition and thickness to prevent antiferromagnetic exchange coupling. The laminated medium has improved thermal stability and reduced intrinsic media noise.

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LAMINATED MAGNETIC RECORDING MEDIA WITH ANTIFERROMAGNETICALLY COUPLED LAYER AS ONE OF THE INDIVIDUAL MAGNETIC LAYERS IN THE LAMINATE

Related Application

This application is a continuation-in-part of application Serial No. 09/626,097 filed July 13, 2000, which is a continuation-in-part of application Serial No. 09/416,364 filed October 8, 1999 (now U.S. patent 6,280,813).

Technical Field

This invention relates generally to magnetic recording media, and more particularly to thermally stable high density media.

Background of the Invention

Conventional magnetic recording media, such as the magnetic recording disks in hard disk drives, typically use a granular ferromagnetic layer, such as a sputterdeposited cobaltplatinum (CoPt) alloy, as the recording medium. Each magnetized domain in the magnetic layer is comprised of many small magnetic grains. The transitions between magnetized domains represent the "bits" of the recorded data. IBM's US patents 4,789,598 and 5,523,173 describe this type of conventional rigid disk.

As the storage density of magnetic recording disks has increased, the product of the remanent magnetization M_r (the magnetic moment per unit volume of ferromagnetic material) and the magnetic layer thickness t has decreased. Similarly, the coercive field or coercivity (H_c) of the magnetic layer has increased. This has led to a decrease in the ratio $M_r t / H_c$. To achieve the reduction in $M_r t$, the thickness t of the magnetic layer can be reduced, but only to a limit because the layer will exhibit increasing magnetic decay, which has been attributed to thermal activation of small magnetic grains (the superparamagnetic effect). The thermal stability of a magnetic grain is to a large extent determined by $K_u V$, where K_u is the magnetic anisotropy constant of the layer and V is the volume of the magnetic grain. As the layer thickness is decreased, V decreases. If the layer thickness is

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too thin, the stored magnetic information will no longer be stable at normal disk drive operating conditions.

One approach to the solution of this problem is to move to a higher anisotropy material (higher K_u). However, the increase in K_u is limited by the point where the coercivity H_c , which is approximately equal to K_u/M_r , becomes too great to be written by a conventional recording head. A similar approach is to reduce the M_r of the magnetic layer for a fixed layer thickness, but this is also limited by the coercivity that can be written. Another solution is to increase the intergranular exchange, so that the effective magnetic volume V of the magnetic grains is increased. However, this approach has been shown to be deleterious to the intrinsic signal/noise ratio (SNR) of the magnetic layer.

Magnetic recording media with high intrinsic SNR (low intrinsic media noise) is desirable because it is well known in metal alloy media, such as CoPt alloys, that the intrinsic media noise increases with increasing linear recording density. Media noise arises from irregularities in the magnetic transitions and results in random shifts of the readback signal peaks. These random shifts are referred to as "peak jitter" or "time jitter". Thus higher media noise leads to higher bit error rates. It is therefore desirable to develop a thin film metal alloy magnetic media that generates noise below a maximum acceptable level so that data can be recorded at maximum linear density. It is known that substantially improved SNR can be achieved by replacing a single magnetic layer with a laminated magnetic layer of two (or more) separate magnetic layers that are spaced apart by a nonmagnetic spacer layer. This discovery was made by S. E. Lambert, et al., "Reduction of Media Noise in Thin Film Metal Media by Lamination", *IEEE Transactions on Magnetics*, Vol. 26, No. 5, September 1990, pp. 2706-2709, and subsequently patented in IBM's U.S. patent 5,051,288. The reduction in media noise by lamination is believed due to a decoupling of the magnetic interaction or exchange coupling between the magnetic layers in the laminate. The use of lamination for noise reduction has been extensively studied to find the favorable spacer layer materials, including Cr, CrV, Mo and Ru, and spacer layer thicknesses, from 5 to 400 Å, that result in the best decoupling of the magnetic layers, and thus the lowest media noise. This work has been reported in papers by E. S. Murdock, et al., "Noise Properties of Multilayered CoAlloy Magnetic Recording Media", *IEEE Transactions on Magnetics*, Vol. 26, No. 5,

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September 1990, pp. 2700-2705; A. Murayama, et al., "Interlayer Exchange Coupling in Co/Cr/Co Double-Layered Recording Films Studied by Spin-Wave Brillouin Scattering", *IEEE Transactions on Magnetics*, Vol. 27, No. 6, November 1991, pp. 50645066; and S. E. Lambert, et al., "Laminated Media Noise for High Density Recording", *IEEE Transactions on Magnetics*, Vol. 29, No. 1, January 1993, pp. 223229.

U.S. patent 5,462,796 and the related paper by E. Teng et al., "Flash Chromium Interlayer for High Performance Disks with Superior Noise and Coercivity Squareness", *IEEE Transactions on Magnetics*, Vol. 29, No. 6, November 1993, pp. 36793681, describe a laminated lownoise disk that uses a discontinuous Cr film that is thick enough to reduce the exchange coupling between the two magnetic layers in the laminate but is so thin that the two magnetic layers are not physically separated.

What is needed is magnetic recording media that will support very high density recording while retaining good thermal stability and SNR.

Summary of the Invention

The invention is a laminated medium for horizontal magnetic recording that includes an antiferromagnetically (AF)coupled magnetic layer as one of the individual magnetic layers and a conventional single magnetic layer as the other individual magnetic layer, with the two magnetic layers separated by a nonferromagnetic spacer layer. The AF-coupled magnetic layer of the laminated medium has two ferromagnetic films exchange coupled antiferromagnetically across a nonferromagnetic spacer film and a net remanent magnetizationthickness product (Mrt) which is the difference in the Mrt values of the two ferromagnetic films. In the AF-coupled magnetic layer, the thickness of the nonferromagnetic spacer film is selected to maximize the strength of the antiferromagnetic exchange coupling between the two ferromagnetic films, resulting in antiparallel alignment of the magnetic moments of the two ferromagnetic films. The individual grains in the ferromagnetic films possess dipole fields which also contribute to the coupling across the spacer film and favor this antiparallel moment alignment. However, in the AF-coupled magnetic layer the strength of the dipole coupling fields is substantially less than the exchange field from the antiferromagnetic exchange coupling.

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In contrast to the nonferromagnetic spacer film in the AF-coupled magnetic layer, the nonferromagnetic spacer layer used to separate the AFcoupled magnetic layer and the single magnetic layer has a thickness to assure that the single magnetic layer is not exchange coupled antiferromagnetically to the nearest ferromagnetic film of the AF-coupled magnetic layer, even though dipole fields are present and can favor antiparallel moment alignment. However, because the dipole fields across the thicker nonferromagnetic spacer layer are less than the coercive field of either the AF-coupled magnetic layer or the single magnetic layer, the magnetic moment of the single magnetic layer and the net magnetic moment of the AF-coupled magnetic layer are oriented parallel in the remanent magnetic states after being saturated in an applied magnetic field.

The AF-coupled magnetic layer can be located below or above the single magnetic layer, with the two magnetic layers separated by the nonferromagnetic spacer layer. The laminated medium can include one or more AF-coupled layers and one or more single magnetic layers in the laminate.

For a fuller understanding of the nature and advantages of the present invention, reference should be made to the following detailed description taken together with the accompanying figures.

Brief Description of the Drawing

Fig. 1 is a schematic sectional view of the antiferromagnetically (AF) coupled magnetic recording layer in a recording medium according to the present invention.

Fig. 2A is a schematic illustration of the AFcoupled layer illustrating the orientations of the moments of the ferromagnetic films at a recorded magnetic transition.

Fig. 2B is a graph of calculated magnetic field above the AFcoupled layer and a single layer (SL) medium as a function of downtrack position from a transition.

Fig. 3 is a schematic sectional view of the disk structure of the present invention illustrating the substrate, underlayer, the films in the AFcoupled layer, and the protective overcoat.

Fig. 4 is a magnetic hysteresis loop for the structure with the AFcoupled layer of Fig. 3.

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Fig. 5 is a schematic sectional view of a prior art laminated disk structure with conventional individual single layers as the magnetic layers in the laminate.

Fig. 6 is a schematic sectional view of a laminated disk structure with AFcoupled layers as the individual magnetic layers in the laminate.

Fig. 7 is a schematic sectional view of a laminated disk structure with an AFcoupled layer as the bottom magnetic layer and a conventional single layer as the top magnetic layer in the laminate.

Fig. 8 is a schematic sectional view of a laminated disk structure with a conventional single layer as the bottom magnetic layer and an AFcoupled layer as the top magnetic layer in the laminate.

Fig. 9 is a schematic illustration of the two-layer laminated medium of Fig. 7 illustrating the orientations of the moments of the single ferromagnetic layer and the two ferromagnetic films of the AFcoupled magnetic layer at a recorded magnetic transition.

Detailed Description of the Invention

The magnetic recording medium of the present invention has a recording layer formed of two or more ferromagnetic films that are exchangecoupled antiferromagnetically (AF) to their neighboring ferromagnetic films by one or more nonferromagnetic spacer films. This is shown schematically in Fig. 1 for a recording layer 10 made up of two ferromagnetic films 12, 14 separated by a nonferromagnetic spacer film 16. The nonferromagnetic spacer film 16 thickness and composition are chosen so that the magnetic moments 22, 24 of adjacent films 12, 14, respectively, are AFcoupled through the nonferromagnetic spacer film 16 and are antiparallel in zero applied fields.

The AF coupling of ferromagnetic films via a nonferromagnetic transition metal spacer film has been extensively studied and described in the literature. In general, the exchange coupling oscillates from ferromagnetic to antiferromagnetic with increasing spacer film thickness. This oscillatory coupling relationship for selected material combinations is described by Parkin et al. in "Oscillations in Exchange Coupling and Magnetoresistance in Metallic Superlattice Structures: Co/Ru, Co/Cr and Fe/Cr", *Phys. Rev. Lett.*, Vol. 64, p. 2034 (1990). The material combinations include ferromagnetic films made of Co, Fe, Ni, and

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their alloys, such as NiFe, NiCo, and FeCo, and nonferromagnetic spacer films such as ruthenium (Ru), chromium (Cr), rhodium (Rh), iridium (Ir), copper (Cu), and their alloys. For each such material combination, the oscillatory exchange coupling relationship has to be determined, if not already known, so that the thickness of the nonferromagnetic spacer film is selected to assure antiferromagnetic coupling between the two ferromagnetic films. The period of oscillation depends on the nonferromagnetic spacer material, but the strength and phase of the oscillatory coupling also depends on the ferromagnetic material and interfacial quality. The oscillatory antiferromagnetic coupling of ferromagnetic films has been used in spinvalve type giant magnetoresistance (GMR) recording heads to design continuous magnetized antiferromagnetically coupled films whose magnetic moments are rigidly coupled together antiparallel during operation of the head. These type of spinvalve structures are described, for example, in IBM patents 5,408,377 and 5,465,185. The '185 patent describes a structure used in many commercially available spinvalve GMR heads, namely a laminated antiparallel pinned ferromagnetic layer having ferromagnetic films whose moments are rigidly coupled together and remain stationary during operation of the head.

The films 12, 14 have magnetic moment values of $Mr_1 t_1$ and $Mr_2 t_2$, respectively. (Because the remanent magnetization Mr is expressed as the magnetic moment per unit volume of ferromagnetic material, the product Mrt is the magnetic moment per unit area for a magnetic layer of thickness t .) For this AFcoupled structure the orientations of the magnetic moments 22, 24 of adjacent films 12, 14, respectively, are aligned antiparallel and thus add destructively to reduce the magnetic moment of the composite layer 10. The arrows 22, 24 represent the moment orientations of individual magnetic domains that are directly above and below one another across the AF coupling film 16. In the absence of an applied magnetic field, when the ferromagnetic film 14 is deposited onto the medium substrate, it will have a granular structure with multiple adjacent grains being coupled together to form individual magnetic domains. In the absence of an applied magnetic field the moments of these domains in film 14 will be essentially randomly oriented. The spacer film or AFcoupling film 16 is then deposited to the correct thickness directly on ferromagnetic film 14. Next, the second ferromagnetic film 12 is deposited directly on the

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AF coupling film 16. As the grains of ferromagnetic film 12 grow they will form magnetic domains with moment orientations that are antiparallel to the moment orientations of ferromagnetic film 14 that are directly across the AF coupling film 16.

The type of ferromagnetic material and the thickness values t_1, t_2 of the ferromagnetic films 12, 14 are chosen so that the net moment in zero applied field will be low, but nonzero. For the case shown in Fig. 1, the M_{rt} for the structure is given by $Mr_1 t_1 Mr_2 t_2$. In the preferred embodiment, $Mr_1 t_1$ should be $> Mr_2 t_2$. This may be accomplished by using the same ferromagnetic materials in the two films 12, 14 and having t_1 be greater than t_2 , or the magnetization (the magnetic moment per unit volume of material) of the two ferromagnetic films may be made different by using different ferromagnetic materials for the two films. While Fig. 1 is shown for a twofilm structure with a single spacer film 16, the invention is extendible to structures with multiple spacer films and multiple ferromagnetic films.

The present invention has a number of advantages over a magnetic layer formed as a single layer of ferromagnetic material. Low remanent magnetization can be obtained without using ultrathin magnetic layers or lowmagnetization alloys. This avoids the problems of thermal instability and difficulty in writing discussed above. If the magnetic layer in Fig. 1 is compared to a singlelayer consisting of only film 12, for example, the addition of the AFcoupled ferromagnetic film 14 reduces the net magnetic moment of the composite structure without decreasing either the thickness or the magnetization of film 12.

The enhanced thermal stability of the composite structure compared to a single magnetic layer arises because the anisotropy of the grains in both films 12 and 14 are substantially uniaxial, and thus can add constructively even if the magnetic moments of films 12, 14 are antiparallel. The resulting stability parameter of the coupled system KuV is given by $Ku_1 V_1 > KuV > (Ku_1 V_1 + Ku_2 V_2)$, where $Ku_1 V_1$ and $Ku_2 V_2$ are the anisotropy energies of typical grains in films 12, 14, respectively. The upper limit for the composite stability parameter $KuV = Ku_1 V_1 + Ku_2 V_2$ will be achieved for the case when magnetic grains in film 12 and 14 are strongly coupled and share a common anisotropy axis direction. The magnetic volume V of the composite structure (layer 10) that determines the thermal stability will be approximately the sum of the volumes of the exchangecoupled grains in films 12 and 14, whereas the magnetic moment of layer 10 is the difference of the individual

moments of films 12, 14. The antiferromagnetic coupling between the two ferromagnetic films provides a mechanism to increase the effective film thickness while reducing the net Mrt value of the composite structure. Thus the ferromagnetic films can contain very small diameter grains and maintain thermal stability.

The AFcoupled medium according to the present invention is shown schematically in Fig. 2A with a recorded or written magnetic transition. The plus (+) and minus () symbols represent the magnetic poles arising from the transition. The calculated longitudinal field (H_x) 10 nm above the surface of the AFcoupled medium is shown in Fig. 2B as a function of X direction or downtrack position from the transition. The moment and thickness values for the two films 12, 14 and the calculated Mrt for the AF-coupled layer are listed in Fig. 2B. For comparison, Fig 2B also shows model calculations of longitudinal magnetic field arising from transitions in a singlелayer (SL) medium that has a similar Mrt. The thickness values (t_1 and t_2) were chosen such that the peak longitudinal field was the same for the AFcoupled medium compared to the SL medium. The total thickness of the ferromagnetic material in the AFcoupled medium is 2.7 times thicker. Therefore, the AFcoupled medium should be more thermally stable than the SL medium. The longitudinal field profile in the downtrack direction decays faster for the AF-coupled medium, resulting in a sharper transition. This indicates that the transitions can be spaced closer than in the SL medium, resulting in a higher linear bit density for the medium. While not shown in Fig. 2B, calculations have also shown that the demagnetization field from a transition within the AFcoupled medium also decreases faster than in the SL medium. In addition, the magnitude and sign of the demagnetization field depends on the Y position (see Fig. 2A) within the medium. Thus for certain Y positions within the medium, the demagnetization field is reduced to zero. Small demagnetization fields are desired because they can affect other transitions and cause the transition to demagnetize itself.

The present invention has been demonstrated using conventional CoPtCrB longitudinal recording media alloys for the ferromagnetic films. An example structure is shown in Fig. 3. The structure was fabricated using conventional sputter deposition equipment and processes. The films forming the structure were grown onto a Cr underlayer deposited onto a substrate of a AlMg disk blank with a nickel-phosphorous (NiP) surface

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coating, with the substrate temperature at approximately 200 °C. The ferromagnetic films are CoPtCrB, with the top film corresponding to film 12 in Fig. 1 being thicker than the bottom ferromagnetic film corresponding to film 14 in Fig. 1 (12 nm vs. 7 nm). The nonferromagnetic spacer film is a 0.6 nm Ru film. As with singlelayer media, it is advantageous to use a granular ferromagnetic material with isolated magnetic grains to lower the media noise. The Ru film thickness was chosen to be at the first antiferromagnetic peak in the oscillatory coupling relationship. For this example, each CoPtCrB ferromagnetic film included an interface film consisting essentially of 0.5 nm of Co at the interface with the Ru film. These ultrathin Co films increase the interfacial moment between the ferromagnetic films and the Ru film, resulting in enhanced antiferromagnetic coupling. However, antiferromagnetic exchange coupling has been demonstrated without incorporating the Co interface films in the CoPtCrB ferromagnetic films.

Fig. 4 shows the major hysteresis loop (solid line) and the remanent hysteresis loop (dashed line) measured at T=350 °K for the structure of Fig. 3. Referring first to the remanent hysteresis loop, it is obtained by saturating the AFcoupled layer in a positive field and then applying an increasing reverse negative field and measuring the remanent moment in the layer after the negative field is applied. The remanent loop is a plot of the remanent moment versus the magnitude of the reverse field. For this sample the remanent loop shows M_{rt}=0.21, the remanent coercive field H_{cr}=3.2 kOe, and S'=0.92 at room temperature, where S' is a measure of the slope of the remanent loop at H_{cr}. For comparison, a similarly grown 15nm single layer of the same CoPtCrB alloy has properties of M_{rt}=0.38, H_{cr}=2.4 kOe and S'=0.76 at room temperature. Thus, the AFcoupled medium allows a significantly lower M_{rt} to be achieved with a greater total magnetic layer thickness.

Referring next to the major hysteresis loop of Fig. 4, the pairs of horizontal arrows indicate the orientation of the ferromagnetic films in the AFcoupled layer at different points in the hysteresis loop. The applied field is increased in the positive direction (arrows 30, 32). For large applied fields (>3000 Oe), the antiferromagnetic coupling is overcome and the moments of the two ferromagnetic films are both parallel to the applied field (arrows 42, 44). As the applied field is reduced (arrow 34) the moment of the thinner bottom ferromagnetic film reverses and becomes antiparallel to the moment of the thicker top

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ferromagnetic film (arrows 52, 54) and to the applied field with a drop in the net moment. This switch occurs roughly at the exchange field felt by the bottom film ($H_{ex2}=2000$ Oe) arising from the coupling across the Ru film. The value of $H_{ex2} = J_{ex}/M_2 t_2$, where J_{ex} is the antiferromagnetic interface exchange energy density across the Ru spacer layer and M_2 and t_2 are the magnetization and thickness of the bottom ferromagnetic film, respectively. For an antiparallel alignment of the ferromagnetic films to be realized requires that H_{ex2} exceed the coercive field required to reverse the bottom ferromagnetic film (H_{c2}). H_{c2} is the coercive field of the bottom film, assuming no exchange interaction with the top ferromagnetic film. Thus, the magnetic properties and thickness of the bottom film, as well as the AFcoupling film, must be designed to maintain $H_{ex2}>H_{c2}$.

The remanent state after saturation in a positive field is given by the moment of the top ferromagnetic film parallel to the field direction and the moment of the bottom ferromagnetic film antiparallel to the positive field direction (arrows 52, 54). In a reverse applied field (arrow 36), the magnetic state is stable until the moment of the top ferromagnetic film reverses and the moments of both films are parallel and aligned in the negative saturation state (arrows 62, 64). The switching of the moment of the top ferromagnetic film determines the coercive field of the AFcoupled layer and is given by $H_c = H_{ex1} + H_{c1}$ where H_{ex1} is the exchange field acting on the top ferromagnetic film ($H_{ex1}=J_{ex}/M_1 t_1$) and H_{c1} is the coercive field of the top ferromagnetic film, assuming no interaction with the bottom ferromagnetic film. Thus, the properties of the top ferromagnetic film and the AFcoupling film must be designed to maintain H_c of the composite structure below the expected write field of the head. For this example the pathway to go from one remanent state (arrows 52, 54) to the next remanent state (arrows 72, 74) goes through an intermediate state where the moments of the two films are parallel (arrows 62, 64). Thus, in contrast to AFcoupled structures used in spinvalve GMR recording heads, the moments of the ferromagnetic films in the medium according to the present invention are not rigidly coupled together across the AFcoupling film because the coupling must be overcome to write on the medium. The hysteresis loop of Fig. 4 exhibits the desired feature of an AFcoupled layer, i.e., a low remanent magnetization relative to the saturation magnetization.

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Recording performance tests on the AFcoupled layer were performed using a conventional longitudinal recording head. Signal to noise ratio measurements determined a media S_oNR of 31.9 dB at 9500 flux changes per millimeter (fc/mm), where S_o is the isolated pulse amplitude and N is the integrated media noise at 9500 fc/mm recording density. These results demonstrate the viability of AFcoupled magnetic layers for data storage.

The AFcoupled media according to the present invention has also been demonstrated for structures with and without one or both Co interface films, with and without one or both CoCr interface layers, and with CoCrPtTa ferromagnetic films.

Laminated Media with AF-coupled Layers

Laminated magnetic recording media, based on the invention described in the previously cited '288 patent, have also been fabricated with the AFcoupled (AFC) layers described above as the individual magnetic layers in the laminate. Fig. 5 is a schematic of a conventional laminated magnetic recording medium wherein the magnetic recording layer 30 comprises at least two individual magnetic layers 32, 34, each with a magnetic moment (per unit area) of M_{rt1}, where two neighboring layers are separated by a nonferromagnetic spacer layer 36. This composite structure has a total M_{rt} = 2M_{rt1} for a twolayer laminate. (For ease in explanation it will be assumed that all ferromagnetic layers have the same composition, so that Mr is the same. However, it is within the scope of the invention that different ferromagnetic materials may be used, in which case the total magnetic moment would be given by M_{r1}t₁ + M_{r2}t₂ for the structure of Fig. 5.)

The new laminated media using the AFC layers is depicted schematically in Fig. 6 for a structure with two AFC layers and one nonferromagnetic spacer layer. In the laminated AFC magnetic media of Fig. 6, the magnetic recording layer 30' comprises AFC layers 32', 34' separated by nonferromagnetic spacer layer 36'. The individual AFC layers 32', 34' replace the corresponding magnetic layers 32, 34 (Fig. 5). Each AFC layer 32', 34' is made up to two films (42, 46 and 52, 56, respectively) antiferromagnetically coupled by antiferromagnetically coupling films (44, 46, respectively) such that the net M_{rt} of each AFC layer is given by M_{rt1}M_{rt2}. This allows control of the M_{rt} independent of either Mr or t. As explained above for the non-laminated AFC media, thermally stable, low M_{rt} magnetic

media can be obtained. In the new laminated structure, as depicted in Fig. 6, the composite Mr_t is 2*(Mr_{t1}Mr_{t2}). By changing the relative magnitude of Mr_{t1} and Mr_{t2}, the Mr_t of the composite laminated structure can be tuned without suffering thermal instabilities. Therefore, thermally stable, low-Mr_t laminated media can be obtained. Of course, while only two AFC layers are depicted in Fig. 6, the laminated AFC media of the present invention may have three or more AFC layers, with nonferromagnetic spacer layers located between neighboring AFC layers.

A series of conventional single-layered media, non-laminated AFC media, and laminated AFC media structures were fabricated on two types of commercially available disk substrates, glass and NiP/AlMg metal, to compare the intrinsic media SNR. The structures on glass substrates were grown on a NiAl/Cr/Co₆₃Cr₃₇ underlayer structure. The structures on NiP/AlMg substrates were grown on a Cr/Co₆₃Cr₃₇ underlayer structure.

For these tests, the magnetic layer composition of all the magnetic films was Co₆₂Pt₁₀Cr₂₂B₆. The antiferromagnetically coupling films 46, 56 used in the AFC layers 32', 34', respectively were 6 Å Ru layers. The nonferromagnetic spacer layer 36' was also Ru, but with thicknesses ranging from 12 to 48 Å. In the laminated AFC media, the nonferromagnetic spacer layer 36' between the two AFC layers 32', 34' is selected to have a composition and thickness so that there is no significant ferromagnetic or antiferromagnetic coupling between the two adjacent ferromagnetic films 44 and 52. For known materials, the thickness of the spacer layer 36' can be readily determined because it is known from the oscillatory coupling curve how the exchange coupling oscillates from ferromagnetic to antiferromagnetic with increasing spacer layer thickness. In the cited '288 patent the Cr spacer film between the two Co alloy films had a thickness of 40 Å or greater, which is well beyond any detectable ferromagnetic or antiferromagnetic exchange coupling peak on the oscillatory coupling curve. For Co₆₂Pt₁₀Cr₂₂B₆ alloy ferromagnetic films and Ru, a Ru thickness greater than approximately 10 Å, which is beyond the first antiferromagnetic peak on the oscillatory coupling curve, is sufficient to assure no significant ferromagnetic or antiferromagnetic coupling. This requirement for the spacer layer is in direct contrast to the requirement for the antiferromagnetic coupling films 46, 56, each of which is selected to have a thickness and composition corresponding to the first antiferromagnetic peak of the

oscillatory coupling curve.

The AFC layers in both the laminated and non-laminated AFC media structures were designed to have an $M_{rt}=M_{rt1}-M_{rt2}=0.20$ memu/cm². The laminated AFC media with two individual AFC layers (Fig. 6) thus had a total $M_{rt}=0.40$ memu/cm². The conventional media with a single CoPtCrB layer was fabricated to have $M_{rt} = 0.38$ memu/cm². The measured SNR for these structures is shown in Table 1 (glass substrates) and Table 2 (metal substrates) below:

Table 1
(Glass Substrates)

<i>SAMPLE</i>	<i>Mrt</i> (memu/cm ²)	<i>Media SNR</i> (dB)
CoPtCrB conventional single layer	0.38	32.3
Non-laminated AFC	0.20	31.5
Laminated AFC/12 A Ru spacer	0.40	33.3
Laminated AFC/24 A Ru spacer	0.40	33.3
Laminated AFC/48 A Ru spacer	0.40	33.2

Table 2
(Metal Substrates)

<i>SAMPLE</i>	<i>Mrt</i> (memu/cm ²)	<i>Media SNR</i> (dB)
Non-laminated AFC	0.24	32.4
Laminated AFC/12 A Ru spacer	0.40	34.6
Laminated AFC/24 A Ru spacer	0.39	34.8
Laminated AFC/36 A Ru spacer	0.40	34.9

For both sets of disks a 1-2 dB improvement in SNR is achieved for the laminated media compared to the non-laminated AFC media and the conventional single layer media.



Laminated Media with AF-coupled Layer and Single Magnetic Layer

Laminated media for horizontal or in-plane magnetic recording based on the invention described in the previously cited '288 patent have also been fabricated using the AFcoupled (AFC) layer described above as one of the individual magnetic layers and a conventional single ferromagnetic layer as the other magnetic layer in a two-magnetic-layer laminate.

The laminated media using the AFC magnetic layer and a single layer is depicted schematically in Fig. 7 for a two-magnetic-layer structure with the AFC layer as the bottom layer and a conventional single magnetic layer above the AFC layer. In the laminated media of Fig. 7, the laminated magnetic recording layer 130 comprises AFC layer 132 and single magnetic layer 134 separated by nonferromagnetic spacer layer 136. The AFC layer 132 replaces the single magnetic layer 32 (Fig. 5). The AFC layer 132 is made up of two films 142 and 144 that are antiferromagnetically coupled by antiferromagnetically coupling film 146, such that the net Mrt of AFC layer 132 is given by Mrt_1Mrt_2 . This allows control of the Mrt independent of either Mr or t. As explained above for the non-laminated AFC media, thermally stable, low Mrt magnetic layers can be obtained. In the new laminated structure, as depicted in Fig. 7, the composite Mrt is $Mrt_s + |(Mrt_1Mrt_2)|$, where Mrt_s is the Mrt of the single magnetic layer 134. If layer 134 and films 142 and 144 all have the same composition then this tuning is accomplished by selecting their desired thicknesses. Therefore, the use of the AFC layer as one of the magnetic layers allows thermally stable, low-Mrt laminated media to be obtained. Of course, since in a laminated medium each of the magnetic layers contributes to the readback signal, the net magnetic moment of the AFC layer must be non-zero, so that Mrt_1 and Mrt_2 are selected to be not equal. The magnetic moment of the single magnetic layer 134 and the net magnetic moment of the AF-coupled magnetic layer 132 are oriented parallel in the remanent magnetic states after being saturated in an applied magnetic field. In Fig. 7, because Mrt_1 is depicted as being greater than Mrt_2 , the moment of layer 134 is shown as being parallel to the moment of film 144. However, if the moment of the lower film 142 of the AFcoupled layer 132 was greater than the moment of upper film 144, then the moment of layer 134 would be parallel to the moment of of film 142 in the remanent magnetic states.

Fig. 8 shows an alternative embodiment for the laminated recording layer 130' wherein the single magnetic layer 134' is the bottom layer and the AFcoupled magnetic layer 132' is above the single layer 134' and spaced from it by nonferromagnetic spacer layer 136'. In this embodiment, like the embodiment of Fig. 7, upper film 144' can have a moment greater than or less than the moment of lower film 142', but in the remanent magnetic states the moment of single layer 134' will be parallel to the film 144' or 142' with the greater moment.

While only a two-magnetic-layer laminated structure is depicted in Figs. 7 and 8, the laminated media of the present invention may have two or more AFC layers and two or more single magnetic layers, with nonferromagnetic spacer layers located between the neighboring magnetic layers.

To demonstrate the improvement in recording performance that can be achieved with **ARC920020003**

this structures a comparison in S_0NR was made with a structure of only an AFC layer. S_0NR is the signal-to-noise ratio of the media, where S_0 is the isolated pulse amplitude and noise amplitude is measured at the recorded density. Both disks were made on commercially available glass disk substrates. The two structures for comparison are described below

1) Media comprising a single AFC layer:

$\text{Cr}_{50}\text{Ti}_{50}/\text{Ru}_{50}\text{Al}_{50}/\text{Cr}_{90}\text{Ti}_{10}/\text{Co}_{89}\text{Cr}_{11}$ ($M_{rt}=0.13 \text{ memu/cm}^2$)/
 $\text{Ru}(6 \text{ \AA})/\text{Co}_{63}\text{Pt}_{12}\text{Cr}_{14}\text{B}_{11}$ ($M_{rt}=0.37 \text{ memu/cm}^2$)/Carbon overcoat

2) Media comprising a two-layer laminate of an AFC layer and a single ferromagnetic layer:

$\text{Cr}_{50}\text{Ti}_{50}/\text{Ru}_{50}\text{Al}_{50}/\text{Cr}_{90}\text{Ti}_{10}/\text{Co}_{89}\text{Cr}_{11}$ ($M_{rt}=0.13 \text{ memu/cm}^2$)/
 $\text{Ru}(6 \text{ \AA})/\text{Co}_{63}\text{Pt}_{12}\text{Cr}_{14}\text{B}_{11}$ ($M_{rt}=0.37 \text{ memu/cm}^2$)/
 $\text{Ru}(12 \text{ \AA})/\text{Co}_{63}\text{Pt}_{12}\text{Cr}_{14}\text{B}_{11}$ ($M_{rt}=0.37 \text{ memu/cm}^2$)/Carbon overcoat

The $\text{Cr}_{50}\text{Ti}_{50}/\text{Ru}_{50}\text{Al}_{50}/\text{Cr}_{90}\text{Ti}_{10}$ is the underlayer structure formed on the substrate and is the same for both structures. The $\text{Co}_{89}\text{Cr}_{11}$ ($M_{rt}=0.13 \text{ memu/cm}^2$)/
 $\text{Ru}(6 \text{ \AA})/\text{Co}_{63}\text{Pt}_{12}\text{Cr}_{14}\text{B}_{11}$ is the AFC layer. In structure 2), which is like that shown in Fig. 7, a $\text{Co}_{63}\text{Pt}_{12}\text{Cr}_{14}\text{B}_{11}$ layer 134 is the single magnetic layer formed on top of the AFC layer 132 and decoupled from the $\text{Co}_{63}\text{Pt}_{12}\text{Cr}_{14}\text{B}_{11}$ film 146 in the AFC layer 132 by the 12 Å Ru nonferromagnetic spacer layer 136. All other growth parameters were identical for the two structures. The total M_{rt} of the single AFC layer structure is 0.24 memu/cm², while the total M_{rt} of the two-layer laminate structure is 0.61 memu/cm².

The measured S_0NR versus recording track density for a disk structure with only the AF-coupled layer was compared with that for the laminated disk structure of the present invention with a two-layer laminate of an AF-coupled layer and a single magnetic layer. The results demonstrated a significant improvement in S_0NR at all recording densities for the two-layer laminate structure with approximately a 2 dB improvement at 250 kilo flux changes/inch (kfc) and approximately a 3.5 dB improvement at 500 kfc.

The antiferromagnetically coupling film used in the AFC layer in both structures 1) and 2) was 6 Å Ru, which is the thickness close to the first antiferromagnetic exchange coupling peak of the oscillatory coupling curve. This peak occurs at a Ru thickness in the range of approximately 5-8 Å. The nonferromagnetic spacer layer in structure 2) was also Ru, but with a thickness of 12 Å. In the two-layer laminate comprising the AFC layer and the single ferromagnetic layer (Fig. 7), the nonferromagnetic spacer layer 136 has a composition and thickness so that there is no significant ferromagnetic or antiferromagnetic coupling between film 144 and layer 134. For known materials, the thickness of the spacer layer 136 can be readily determined. This is because it is known from the oscillatory coupling curve that as the spacer layer thickness increases the exchange coupling oscillates from antiferromagnetic to ferromagnetic with decreasing magnitude. In the cited '288 patent the Cr spacer film between the two Co alloy films had a thickness of 40 Å or greater, which

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is well beyond any detectable ferromagnetic or antiferromagnetic exchange coupling peak on the oscillatory coupling curve. For granular cobalt alloys, such as CoPtCrB alloys, and a Ru antiferromagnetically coupling film, the oscillatory peaks other than the first antiferromagnetic peak decrease rapidly with Ru thickness and are barely detectable, so that a Ru thickness greater than approximately 10 Å, which is beyond the first antiferromagnetic peak of about 6 Å, is sufficient to conclude that there would be no exchange coupling. Thus the spacer layer 136 is selected to have a composition and thickness in direct contrast to that for the antiferromagnetic coupling film 146, which is selected to have a composition and thickness corresponding to the first antiferromagnetic peak of the oscillatory coupling curve.

In the AF-coupled magnetic layer 132, the individual grains in the ferromagnetic films 142, 144 possess dipole fields which also contribute to the coupling across the spacer film 146 and favor antiparallel moment alignment of films 142 and 144, but the strength of these dipole coupling fields is substantially less than the exchange field from the antiferromagnetic exchange coupling. Dipole fields from layer 132 and layer 134 are also present and would tend to favor antiparallel moment alignment between these layers, but the nonferromagnetic spacer layer 136 in the laminated medium has a thickness to assure that layer 134 is not exchange coupled antiferromagnetically to film 144. Because the dipolar fields across the thicker nonferromagnetic spacer layer 136 are less than the coercive field of either layer 132 or layer 134, the magnetic moment of the single magnetic layer 134 and the net magnetic moment of the AF-coupled magnetic layer 132 are oriented parallel in the remanent magnetic states after being saturated in an magnetic applied field.

The orientations of the moments of the single ferromagnetic layer 134 and the two ferromagnetic films 142, 144 of the AF-coupled magnetic layer at a recorded magnetic transition are depicted in Fig. 9 for the two-layer laminated medium shown in Fig. 7. The moment orientations on the two sides of the transition also illustrate the orientations of the moments in the two remanent magnetic states (zero applied field).

While the present invention has been particularly shown and described with reference to the preferred embodiments, it will be understood by those skilled in the art that various changes in form and detail may be made without departing from the spirit, scope, and teaching of the invention. Accordingly, the disclosed invention is to be considered merely as illustrative and limited in scope only as specified in the appended claims.

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What is claimed is:

1. A magnetic recording medium comprising:

a substrate;

a magnetic recording layer on the substrate and comprising an antiferromagnetically coupled (AFC) layer, a ferromagnetic layer and a nonferromagnetic spacer layer separating the AFC layer and the ferromagnetic layer, the AFC layer comprising a first ferromagnetic film, a second ferromagnetic film and an antiferromagnetically coupling film located between the first and second ferromagnetic films and having a thickness and composition to provide antiferromagnetic exchange coupling of the first and second ferromagnetic films, the nonferromagnetic spacer layer being located between the second ferromagnetic film of the AFC layer and the ferromagnetic layer and having a thickness and composition wherein the ferromagnetic layer and the second ferromagnetic film of the AFC layer are not exchange coupled.

2. The medium of claim 1 wherein the ferromagnetic layer is located between the substrate and the nonferromagnetic spacer layer and the AFC layer is located on the nonferromagnetic spacer layer.

3. The medium of claim 1 wherein the ferromagnetic layer is a first ferromagnetic layer and further comprising a second ferromagnetic layer and a second nonferromagnetic spacer layer located between the first ferromagnetic layer and the second ferromagnetic layer and having a thickness and composition wherein the first and second ferromagnetic layers

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are not exchange coupled.

4. The medium of claim 1 further comprising a second AFC layer and a second nonferromagnetic spacer layer located between the ferromagnetic layer and the first ferromagnetic film of the second AFC layer, the second nonferromagnetic spacer layer having a thickness and composition wherein the ferromagnetic layer and the first film of the second AFC layer are not exchange coupled.

5. The medium of claim 1 wherein the first ferromagnetic film of the AFC layer has a thickness t_1 and a magnetization M_1 , the second ferromagnetic film of the AFC layer has a thickness t_2 and a magnetization M_2 , and wherein the magnetic moments per unit area $(M_1 \times t_1)$ and $(M_2 \times t_2)$ of the first and second ferromagnetic films of the AFC layer, respectively, are different from one another.

6. The medium of claim 5 wherein the first and second ferromagnetic films of the first AFC layer are formed of the same material, and wherein t_1 is different from t_2 .

7. The medium of claim 5 wherein the first and second ferromagnetic films of the first AFC layer are formed of different materials and wherein t_1 and t_2 are substantially the same thickness.

8. The medium of claim 1 wherein antiferromagnetically coupling film of the AFC layer is formed of a material selected from the group consisting of ruthenium (Ru), chromium (Cr), rhodium (Rh), iridium (Ir), copper (Cu), and their alloys.

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9. The medium of claim 1 wherein the first and second ferromagnetic films of the AFC layer are made of a material selected from the group consisting of Co, Fe, Ni, and their alloys.
10. The medium of claim 1 wherein the first ferromagnetic film of the AFC layer includes an interface film consisting essentially of cobalt located at the interface of the first ferromagnetic film and the antiferromagnetically coupling film.
11. The medium of claim 1 wherein the second ferromagnetic film of the AFC layer includes an interface film consisting essentially of cobalt located at the interface of the second ferromagnetic film and the antiferromagnetically coupling film.
12. The medium of claim 1 further comprising an underlayer located on the substrate between the substrate and the magnetic recording layer.
13. The medium of claim 1 further comprising a protective overcoat formed over the magnetic recording layer.
14. The medium of claim 1 wherein the second ferromagnetic film of the AFC layer and the ferromagnetic layer each comprises a granular cobalt-platinum alloy and wherein the nonferromagnetic spacer layer is Ru having a thickness greater than 10 Å.
15. A laminated magnetic recording medium comprising: a substrate; a magnetic recording layer on the substrate and comprising an antiferromagneticallycoupled (AFC) layer, a ferromagnetic layer having a magnetic moment per unit area, and a nonferromagnetic spacer layer separating the AFC layer and the ferromagnetic layer; the AFC layer comprising a first ferromagnetic film, a nonferromagnetic spacer film on the first

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ferromagnetic film, and a second ferromagnetic film exchange coupled antiferromagnetically to the first ferromagnetic film across the spacer film, one of the first and second ferromagnetic films having a magnetic moment per unit area greater than the magnetic moment per unit area of the other ferromagnetic film; the magnetic recording layer exhibiting a major hysteresis loop with two remanent magnetic states in the absence of an applied magnetic field, wherein the orientations of the moments of the first and second ferromagnetic films are antiparallel in each remanent state but the first ferromagnetic film's moment orientation in one remanent state is antiparallel to its orientation in the other remanent state, and the orientations of the moments of the ferromagnetic layer and the greatermoment ferromagnetic film are parallel in both remanent states.

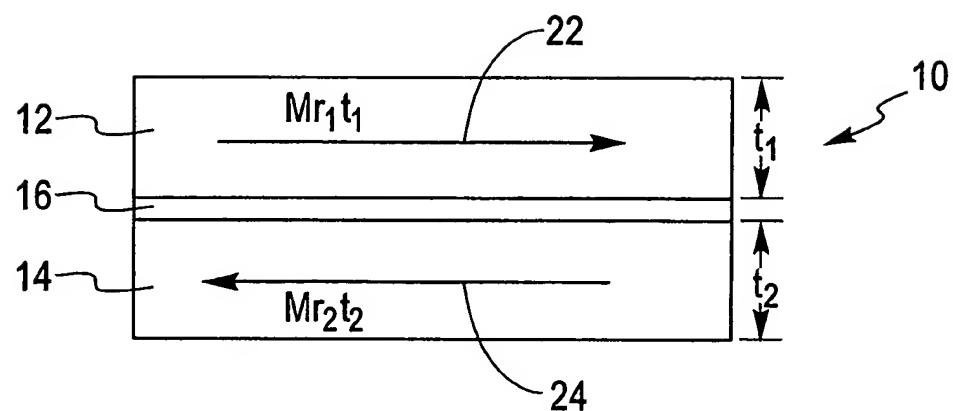
16. The medium of claim 15 wherein the AFC layer is located on the substrate, the nonferromagnetic spacer layer is located over the AFC layer and the ferromagnetic layer is located over the spacer layer.

17. The medium of claim 16 wherein the upper ferromagnetic film of the AFC layer has a moment greater than the lower ferromagnetic film.

18. The medium of claim 17 wherein the lower ferromagnetic film of the AFC layer comprises a CoCr alloy, the nonferromagnetic spacer film of the AFC layer comprises Ru having a thickness between 5-8 Å, the upper ferromagnetic film of the AFC comprises a CoCrPtB alloy, the nonferromagnetic spacer layer comprises Ru having a thickness greater than 10 Å, and the ferromagnetic layer comprises a CoCrPtB alloy.

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**Fig. 1**

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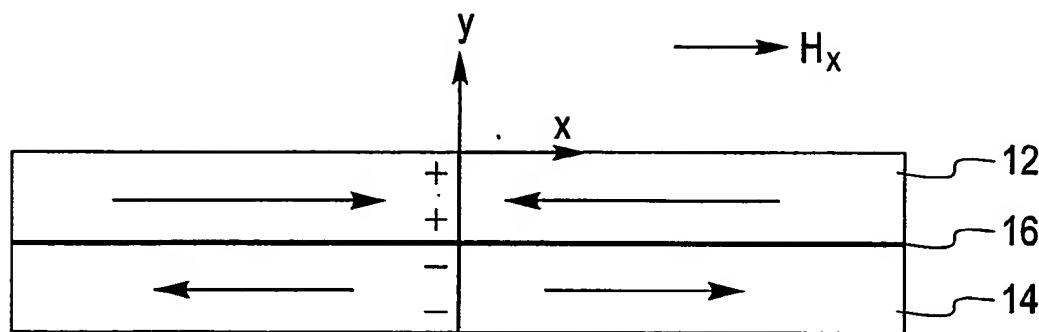


Fig. 2A

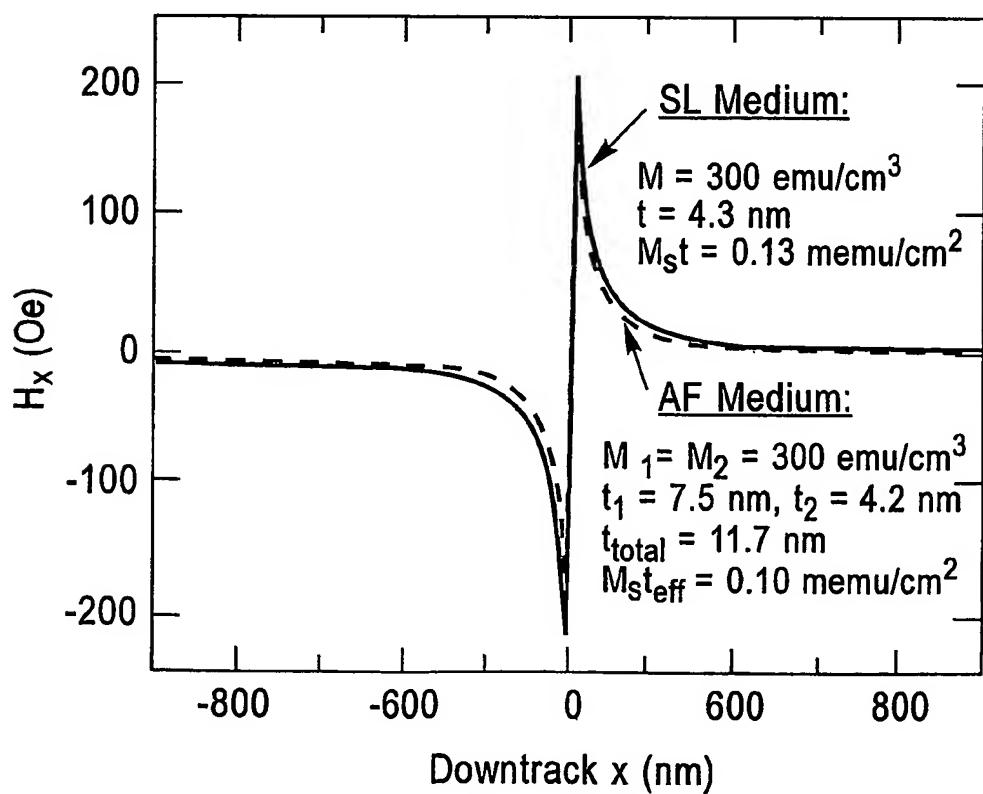
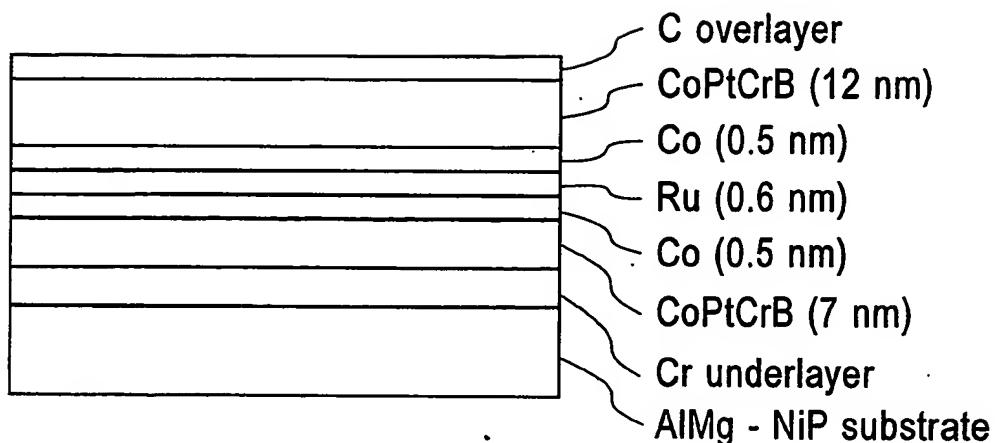
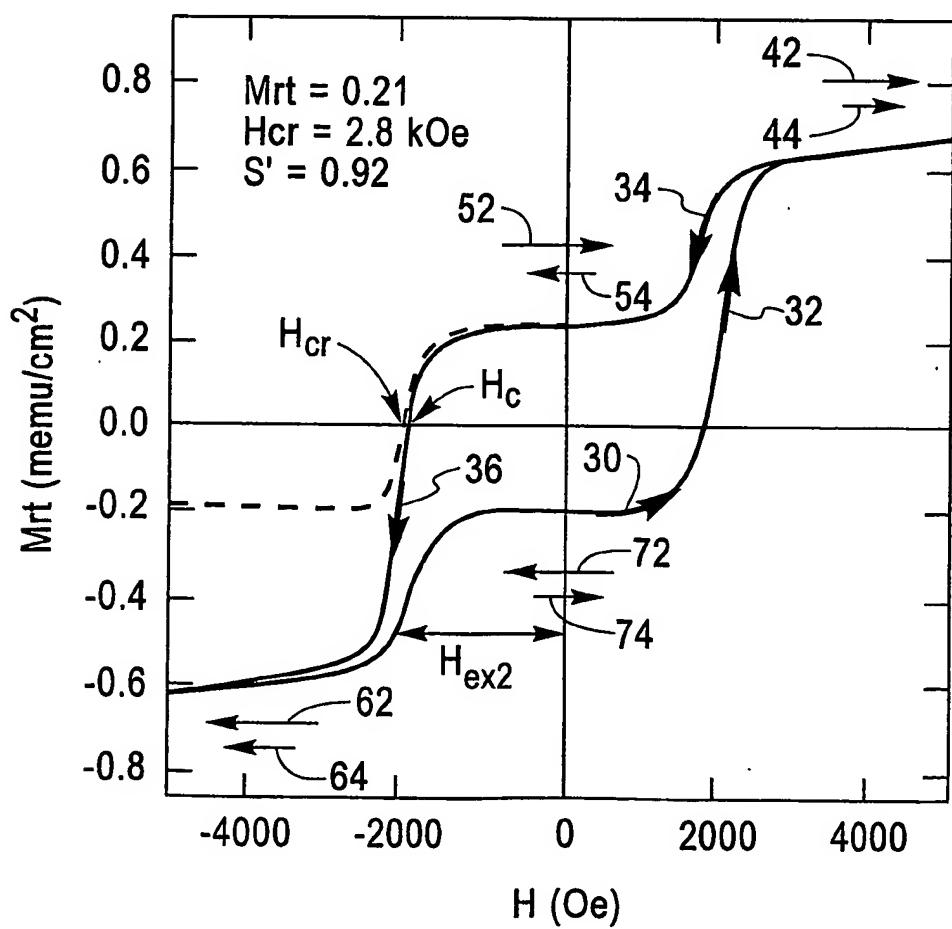


Fig. 2B

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**Fig. 3****Fig. 4**

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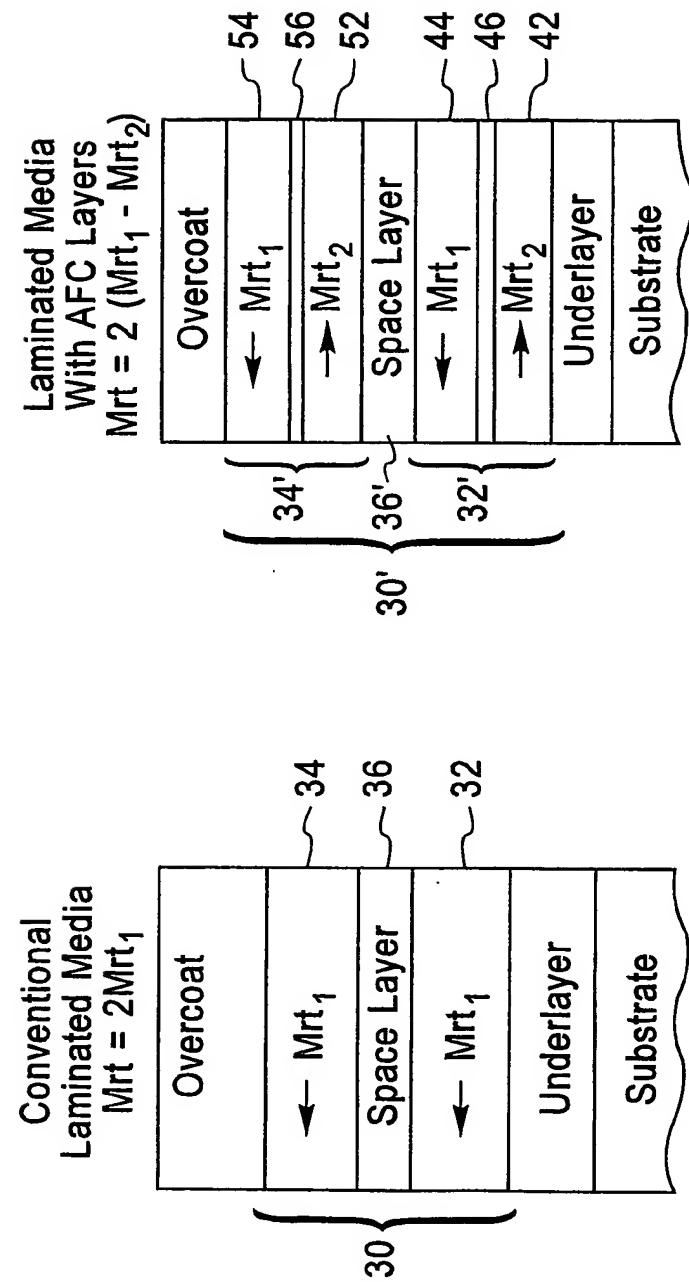
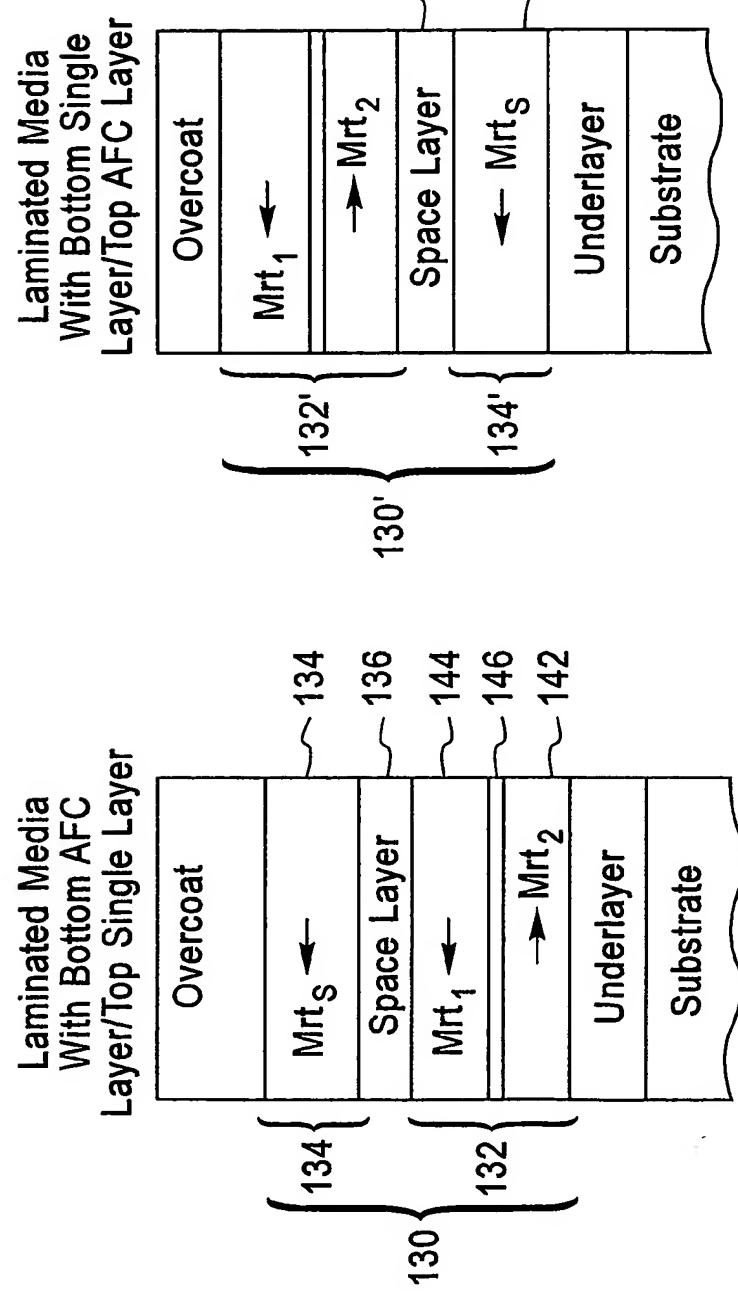


Fig. 5
(Prior Art)

Fig. 6

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**Fig. 7****Fig. 8**

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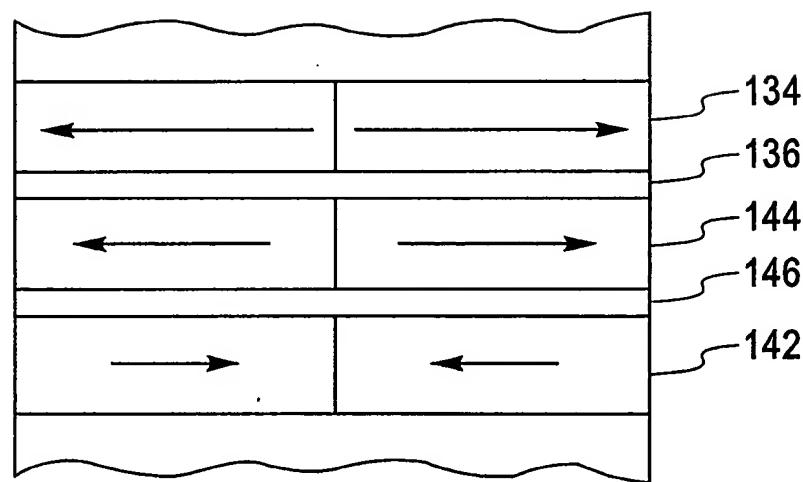


Fig. 9

INTERNATIONAL SEARCH REPORT

International application No.

PCT/US03/02801

A. CLASSIFICATION OF SUBJECT MATTER

IPC(7) : G11B 5/66, 5/70; H01J 1/00
US CL : 428/694TM, 694TS, 611, 900, 336

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
U.S. : 428/694TM, 694TS, 611, 900, 336

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)
EAST

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 5,462,796 A (TENG et al) 31 October 1995 (31.10.95), abstract, figure 1.	1-18
A	US 5,465,185 A (HEIM et al) 07 November 1995 (07.11.95), abstract, figure 5.	1-18
A	PARKIN. S.S.P Oscillations in Exchange Coupling and Magnetoresistance in Metallic Superlattice Structures: Co/Ru, Co/Cr, and Fe/Cr, Cal Review Letters, 07 May 1990, Vol. 64, No. 19, pages 2304-2307.	1-18

<input type="checkbox"/>	Further documents are listed in the continuation of Box C.	<input type="checkbox"/>	See patent family annex.
*	Special categories of cited documents:	"T"	later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
"A"	document defining the general state of the art which is not considered to be of particular relevance	"X"	document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
"E"	earlier application or patent published on or after the international filing date	"Y"	document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
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"O"	document referring to an oral disclosure, use, exhibition or other means		
"P"	document published prior to the international filing date but later than the priority date claimed		

Date of the actual completion of the international search 07 April 2003 (07.04.2003)	Date of mailing of the international search report 24 APR 2003
Name and mailing address of the ISA/US Commissioner of Patents and Trademarks Box PCT Washington, D.C. 20231 Facsimile No. (703)305-3230	Authorized officer Holly Rickman Telephone No. (703) 308-0661 <i>[Signature]</i>

Form PCT/ISA/210 (second sheet) (July 1998)

